







## **IF3601 N-Channel JFET**

#### **Features**

InterFET N3600L Geometry

Ultra Low Noise: 0.35 nV/VHz Typical

High Gain: 175mS TypicalLow Rds(on): 2.0 Ohms Typical

RoHS Compliant

• SMT, TH, and Bare Die Package options.

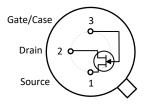
### **Applications**

· Low-Noise, High Gain Amplifiers

#### Description

The -20V InterFET IF3601 JFET is targeted for ultra low noise high gain amplifier designs. The IF3601 has a cutoff voltage of less than 2.0V ideal for low voltage applications. The TO-39 package is hermetically sealed and suitable for military applications.

#### **TO-39 Bottom View**





**Product Summary** 

	Parameters	IFN3601 Min	Unit	
BV <sub>GSS</sub>	Gate to Source Breakdown Voltage	-20	V	
I <sub>DSS</sub>	Drain to Source Saturation Current	30	mA	
V <sub>GS(off)</sub>	Gate to Source Cutoff Voltage	-0.35	V	
GFS	Forward Transconductance	175 Typical	mS	

Ordering Information Custom Part and Binning Options Available

Part Number	Description	Case	Packaging
IF3601T39	Through-Hole	TO-39	Bulk
IF3601COT	Chip Orientated Tray (COT Waffle Pack)	COT	100/Waffle Pack
IF3601CFT	Chip Face-up Tray (CFT Waffle Pack)	CFT	100/Waffle Pack



**Disclaimer:** It is the Buyers responsibility for designing, validating and testing the end application under all field use cases and extreme use conditions. Guaranteeing the application meets required standards, regulatory compliance, and all safety and security requirements is the responsibility of the Buyer. These resources are subject to change without notice.









## **Electrical Characteristics**

Maximum Ratings (@ T<sub>A</sub> = 25°C, Unless otherwise specified)

	Parameters	Value	Unit
$V_{RGS}$	Reverse Gate Source and Gate Drain Voltage	-20	V
I <sub>FG</sub>	Continuous Forward Gate Current	10	mA
PD	Continuous Device Power Dissipation	300	mW
Р	Power Derating	2	mW/°C
Τı	Operating Junction Temperature	-55 to 125	°C
T <sub>STG</sub>	Storage Temperature	-65 to 200	°C

Static Characteristics (@ TA = 25°C, Unless otherwise specified)

	Parameters	Conditions	Min	Тур	Max	Unit
V <sub>(BR)GSS</sub>	Gate to Source Breakdown Voltage	$V_{DS} = 0V$ , $I_{G} = -1\mu A$	-20			V
I <sub>GSS</sub>	Gate to Source Reverse Current	$V_{GS} = -10V, V_{DS} = 0V$			-0.1	nA
V <sub>GS(OFF)</sub>	Gate to Source Cutoff Voltage	V <sub>DS</sub> = 10V, I <sub>D</sub> = 0.5nA	-0.35		-2.0	V
I <sub>DSS</sub>	Drain to Source Saturation Current	$V_{GS} = 0V$ , $V_{DS} = 10V$ (Pulsed)	30	300		mA

**Dvnamic Characteristics** (@ TA = 25°C, Unless otherwise specified)

	Parameters	Conditions	Min	Тур	Max	Unit
GFS	Forward Transconductance	$V_{DS} = 10V, V_{GS} = 0V, f = 1kHz$		175		mS
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> = 0V, V <sub>GS</sub> = -4V, f = 1MHz		650		pF
Crss	Reverse Transfer Capacitance	V <sub>DS</sub> = 0V, V <sub>GS</sub> = -4V, f = 1MHz		80		рF
en	Equivalent Circuit Input Noise Voltage	V <sub>DS</sub> = 3V, I <sub>D</sub> = 5mA, f = 100Hz		0.35		nV/√Hz

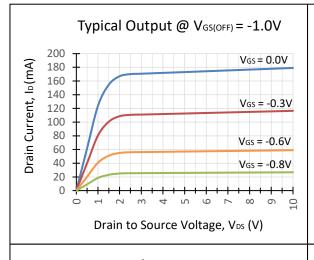


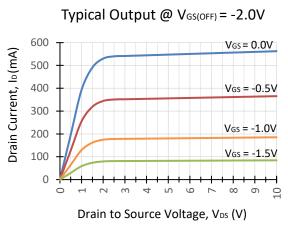


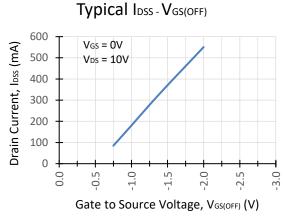


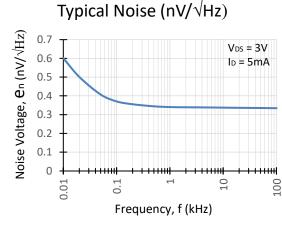


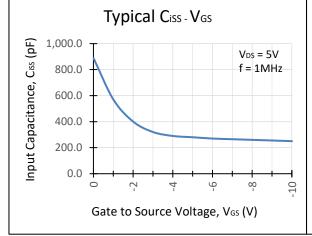
# **Typical IF3601 Characteristics**

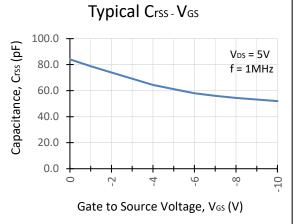














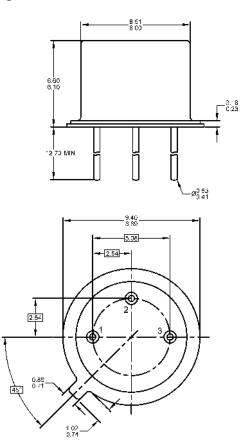




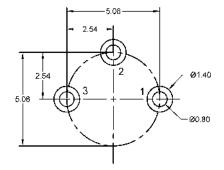


## **TO-39 Mechanical and Layout Data**

## **Package Outline Data**



**Suggested Through-Hole Layout** 



- 1. All linear dimensions are in millimeters.
- 2. Package weight approximately 0.42 grams
- Bulk product is shipped in standard ESD shipping material
- 4. Refer to JEDEC standards for additional information.

- 1. All linear dimensions are in millimeters.
- The suggested land pattern dimensions have been provided as a straight lead reference only. A more robust pattern may be desired for wave soldering and/or bent lead configurations.